

CLAIM AMENDMENTS

Claims 1-30 (Canceled).

31. (Currently Amended) A packaged integrated circuit device comprising:

a plurality of solder ball bond pads, said solder ball bond pads coupled to solder balls;

a plurality of wire bond bond pads, said wire bond bond pads coupled to bonding wires; [[and]]

a first gold coating on said solder ball bond pads and on said wire bond bond pads, the first gold coating on said solder ball bond pads being thinner than the gold coating on said wire bond bond pads; 0.25 microns to about 0.3 microns thick; and

a second gold coating on said wire bond bond pads, said second gold coating and said first gold coating to form a composite gold coating.

32. (Currently Amended) The device of claim 31 wherein the thickness of the first gold coating on said solder ball bond pads is sufficiently low to reduce the likelihood of solder ball joint embrittlement.

Claims 33 and 34 (Canceled)

35. (Currently Amended) The device of claim [[33]] 31 wherein said the composite gold coating on said wire bond bond pads has a thickness of approximately 0.5 microns.

36. (Original) The device of claim 31 wherein said solder ball bond pads and said wire bond bond pads are all contained on the same planar surface.

37. (Currently Amended) A device comprising:

a first and second bond pad, said first and second bond pads comprising a nickel coated metal; [[and]]

a first gold coating on said first and second bond pads, the first gold coating on said first bond pad thinner than the gold coating on said second bond pad; 0.25 to about 0.3 microns thick; and

a second gold coating on said second bond pads, said second gold coating and said first gold coating forming a composite gold coating.

38. (Previously Presented) The device of claim 37 wherein the first bond pad comprises a nickel coated copper.

39. (Previously Presented) The device of claim 38 wherein the second bond pad comprises a nickel coated aluminum.

Claims 40 and 41 (Canceled)

42. (Currently Amended) The device of claim 37 wherein the composite gold coating on the second bond pad has a thickness of about 0.5 microns.

43. (Previously Presented) The device of claim 37 wherein the first and second bond pads coexist on a planar support structure.

44. (Previously Presented) An intermediate structure for an integrated circuit device comprising:

a first bond pad comprising a gold coated metal, said gold coating having a thickness of between about 0.1 and 0.5 microns; and

a second bond pad which is masked, said second bond pad comprising a nickel coated metal.

45. (Previously Presented) The structure of claim 44 wherein the metal of said first bond pad comprises a nickel coated aluminum.

46. (Previously Presented) The structure of claim 44 wherein said second bond pad comprises a nickel coated copper.

47. (Previously Presented) The structure of claim 44 wherein said first and second bond pads are on the same planar surface.

48. (New) The device of claim 31 wherein the solder ball bond pads include nickel coated copper.

49. (New) The device of claim 48 wherein the wire bond pads include nickel coated aluminum.